

4 Quadrants photodiode with hole

Specifications

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| Detection material: | n/P, 10 ... 20 Ohmcm, 525 μm |
| Active area: | 1.24 mm ² per quadrant |
| Spectral range: | 200 nm ... 1150 nm |
| Wavelength of peak response: | 800 nm |
| Storage temperature: | -40 °C ... 150 °C |
| Dark current I_{R} : (max at -5 V) | 2 nA/mm ² |
| Junction capacitance C_{j} : (max at -5 V) | 30 pF/mm ² |
| Top bondpad material: | AlSi |
| Top bondpad size: | 300 μm \times 300 μm |
| Bottom material: | AlSi |